

APPL NUM 10612028	FILING DATE 07/02/2003	CLASS 257	SUBCLASS 266.000	GAU 2814	EXAMINER PHAM, L
<b>**APPLICANTS:</b> Kang-Soo Chu; Joo-Won Lee; Jae-Eun Park; Jong-Ho Yang;					
<b>**CONTINUING DATA VERIFIED:</b>  <div style="text-align: center; font-family: cursive; font-size: 1.2em;">None</div>					
<b>** FOREIGN APPLICATIONS VERIFIED:</b> REPUBLIC OF KOREA 02-55005 09/11/2002					
PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>			
Foreign priority claimed 35 USC 119 conditions met		<input checked="" type="checkbox"/> yes <input type="checkbox"/> no <input checked="" type="checkbox"/> yes <input type="checkbox"/> no		ATTORNEY DOCKET NO SAM-0421	
Verified and Acknowledged Examiners's initials <div style="font-family: cursive; font-size: 1.2em;">LP</div>		<b>TITLE :</b> Semiconductor device having an etch stopper formed of a SiN layer by low temperature ALD and method of fabricating the same			